

MAY 01 2007

- 2 -

Application No. 10/801,542
Docket No. 74075-2717**Amendments to the Claims:**

1. (Original) A display device comprising:
plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;
wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.
2. (Original) A display device according to claim 1, the channel length of the first thin film transistor and the second thin film transistor is at least 5 times as long as a gate width, respectively.
3. (Original) A display device according to claim 1, the first thin film transistor and the second thin film transistor comprises a semiconductor layer which is formed by irradiating with a pulsed laser beam.
4. (Original) A display device comprising:
plural groups including a thin film transistor and a light emitting element in which brightness is fluctuated depending on an ON current value in a saturation region of a drain voltage-drain current characteristic of the thin film transistor;
wherein an absolute value of a fluctuation rate in an ON current value in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12 %.
5. (Currently Amended) A display device according to claim [[2]] 4, the channel length of the first thin film transistor and the second thin film transistor is at least 5 times as long as a gate width, respectively.

- 3 -

Application No. 10/801,542
Docket No. 74075-2717

6. (Currently Amended) A display device according to claim ~~[[2]]~~ 4, the first thin film transistor and the second thin film transistor comprises a semiconductor layer which is formed by irradiating with a pulsed laser beam.

7. (Original) A display device comprising plural pixels including a driving thin film transistor, a switching thin film transistor, an erasing thin film transistor, a light emitting element which is connected to the driving thin film transistor;

wherein brightness is fluctuated depending on an ON current value in a saturation region of a drain voltage-drain current characteristic of the driving thin film transistor; and,

an absolute value of a fluctuation rate of the ON current value in a saturation region of the driving thin film transistor included in each a first pixel and a second pixel which is adjacent to the first pixel is at most 12%.

8. (Original) A display device according to claim 7, a channel length of the driving thin film transistor is at least 5 times as long as a gate width.

9. (Original) A display device according to claim 7, the driving thin film transistor comprises a semiconductor layer formed by irradiating with a pulsed laser beam.

10. (Original) An electronic device having the display device according to claim 1; wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a mobile telephone.

11. (Original) An electronic device having the display device according to claim 4; wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a mobile telephone.

12. (Original) An electronic device having the display device according to claim 7;

- 4 -

Application No. 10/801,542
Docket No. 74075-2717

wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a cellular phone.

13. (Original) A cellular phone comprising a main body, a display portion, a voice output portion, an operation switch, and an antenna;

said cellular phone comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

14. (Original) A notebook computer comprising a main body, a case, a display portion, and a keyboard;

said notebook computer comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

15. (Original) A semiconductor device comprising:

plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;

wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.

- 5 -

Application No. 10/801,542
Docket No. 74075-2717

16. (Original) An electronic device having the semiconductor device according to claim 15;

wherein said electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a cellular phone.